

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	198	(double near2 triggered near2 silicon near2 controlling near2 rectifier) or (DT near2 SCR) or (Double near3 SCR).clm.	US-PGPUB; USPAT; JPO	OR	ON	2005/12/14 13:25
L2	465	(double with triggered with silicon with controlling with rectifier) or (DT with SCR) or (Double with SCR).clm.	US-PGPUB; USPAT; JPO	OR	ON	2005/12/14 13:26
L3	26	((double with triggered with silicon with controlling with rectifier) or (DT with SCR) or (Double with SCR)).clm.	US-PGPUB; USPAT; JPO	OR	ON	2005/12/14 13:35
L4	15	((double with triggered with silicon with controlling with rectifier) or (DT with SCR) or (Double with SCR) and isolation).clm.	US-PGPUB; USPAT; JPO	OR	ON	2005/12/14 13:37
L5	15	(anode and cathode and (double with triggered with silicon with controlling with rectifier) or (DT with SCR) or (Double with SCR) and isolation).clm.	US-PGPUB; USPAT; JPO	OR	ON	2005/12/14 13:39
S1	2	"20050133869"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/12 11:09
S2	6666	((257/118,244,328-333,466,513,594) or (438/242,268-274)).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/12 09:23
S3	49	S2 and (SCR or "silicon controller rectifier")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/12 11:17
S4	21775	(ESD or "electrostatic discharge")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/12 11:18
S5	1176	(ESD or "electrostatic discharge") and (SCR or "silicon controlling rectifier")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/12 11:19

S6	7	(ESD or "electrostatic discharge") and (SCR or "silicon controlling rectifier") and (double near trigg\$4)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/12 11:33
S7	2365	(361/56).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/12 11:33
S8	212	S7 and ESD and SCR	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/12 11:33
S9	24050	'silicon controller rectifier' or SCR or 'double triggered silicon controller rectifier' or DTSCR or 'DT SCR'	US-PGPUB; USPAT; JPO	OR	ON	2005/12/13 14:11
S10	4379	S9 and isolation	US-PGPUB; USPAT; JPO	OR	ON	2005/12/13 14:11
S11	393	S9 and ('shallow trench isolation' or STI)	US-PGPUB; USPAT; JPO	OR	ON	2005/12/13 14:45
S12	20	S9 and ('shallow trench isolation' or STI) and ("dummy gate" or DG)	US-PGPUB; USPAT; JPO	OR	ON	2005/12/13 14:12
S13	19	("4939616"   "5012317"   "5225702"   "5281842"   "5465189"   "5602404"   "5622885"   "5719733"   "5754381"   "5856214"   "5903420"   "6081002"   "6172403"   "6184557"   "6207998"   "6228704"   "6423589"   "6465848"   "6482692").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/12/13 14:15
S14	362	Ker.in.	US-PGPUB; USPAT; JPO	OR	ON	2005/12/13 14:54
S15	9481	hsu.in.	US-PGPUB; USPAT; JPO	OR	ON	2005/12/13 14:46
S16	108	S14 and isolation	US-PGPUB; USPAT; JPO	OR	ON	2005/12/13 14:47
S17	1179	S15 and isolation	US-PGPUB; USPAT; JPO	OR	ON	2005/12/13 15:13
S18	7	S15 and isolation and (SCR or 'silicon controller recitifier')	US-PGPUB; USPAT; JPO	OR	ON	2005/12/13 14:47
S19	0	"Ker.in.6" not S16	US-PGPUB; USPAT; JPO	OR	ON	2005/12/13 14:54

S20	254	S14 not S16	US-PGPUB; USPAT; JPO	OR	ON	2005/12/13 14:54
S21	9470	S15 not S14	US-PGPUB; USPAT; JPO	OR	ON	2005/12/13 15:13
S22	1174	S17 not S14	US-PGPUB; USPAT; JPO	OR	ON	2005/12/13 16:08
S23	2168	257/355	US-PGPUB; USPAT; JPO	OR	ON	2005/12/13 16:08
S24	2063	S23 not S17 not S14	US-PGPUB; USPAT; JPO	OR	ON	2005/12/14 09:35
S25	245	257/256	US-PGPUB; USPAT; JPO	OR	ON	2005/12/13 16:12
S26	990	257/356	US-PGPUB; USPAT; JPO	OR	ON	2005/12/13 16:33
S27	1	("5461338").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/12/14 08:23
S28	21	("5900665").URPN.	USPAT	OR	ON	2005/12/14 08:23
S29	362	Ker.in.	US-PGPUB; USPAT; JPO	OR	ON	2005/12/14 09:35
S30	9481	hsu.in.	US-PGPUB; USPAT; JPO	OR	ON	2005/12/14 09:35
S31	1179	S30 and isolation	US-PGPUB; USPAT; JPO	OR	ON	2005/12/14 09:35
S32	2168	257/355	US-PGPUB; USPAT; JPO	OR	ON	2005/12/14 09:35
S33	2063	S32 not S31 not S29	US-PGPUB; USPAT; JPO	OR	ON	2005/12/14 09:35
S34	990	257/356	US-PGPUB; USPAT; JPO	OR	ON	2005/12/14 09:35
S35	314	S34 not S33	US-PGPUB; USPAT; JPO	OR	ON	2005/12/14 10:44
S36	2707115	double naer2 triggered naer2 silicon naer2 controlling naer2 rectifier	US-PGPUB; USPAT; JPO	OR	ON	2005/12/14 10:45
S37	1	double near2 triggered near2 silicon near2 controlling near2 rectifier	US-PGPUB; USPAT; JPO	OR	ON	2005/12/14 10:45

S38	236	(double near2 triggered near2 silicon near2 controlling near2 rectifier) or (DT near2 SCR) or (Double near3 SCR)	US-PGPUB; USPAT; JPO	OR	ON	2005/12/14 13:24
S39	5	silicon near3 rectifier and sixth near3 diffusion isolation near sutrctures.clm.	US-PGPUB; USPAT; JPO	OR	ON	2005/12/14 11:40
S40	2747	'Taiwan Semiconductor Manufacturing Company'.as.	US-PGPUB; USPAT; JPO	OR	ON	2005/12/14 11:40
S41	10	S40 and SCR and STI	US-PGPUB; USPAT; JPO	OR	ON	2005/12/14 11:41